

**REMARKS**

Claim 1 has been amended to recite portions of the subject matter of claim 4, which is canceled herein. Claims 6 and 8 have been amended to correct grammatical errors. Claims 7 and 11 have been amended to improve antecedent basis. Allowed claim 14 has been amended to improve antecedent basis. Allowed claims 15, 19, and 21 have been amended to correct grammatical errors. No new matter has been added.

The Office Action mailed August 14, 2006, has been received and reviewed. Claims 1-21 are currently pending in the application. Claims 1-11 stand rejected. Claims 12-21 are allowed, which is noted with appreciation. Applicants have amended claims 1, 6-8, 11, 14, 15, 19, and 21, canceled claims 2-4, 9, and 10, and respectfully request reconsideration of the application as amended herein.

**35 U.S.C. § 112 Claim Rejections**

Claims 9 and 10 stand rejected under 35 U.S.C. § 112, first paragraph, as allegedly failing to comply with the written description requirement. Applicants have canceled claims 9 and 10, rendering moot this rejection.

**35 U.S.C. § 102(e) Anticipation Rejections**

**Anticipation Rejection Based on U.S. Patent No. 6,190,911 to Gofuku**

Claims 1-4, 6, and 11 stand rejected under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent No. 6,190,911 to Gofuku (“Gofuku”). Claims 2-4 have been canceled, rendering moot the rejection as to these claims. Applicants respectfully traverse this rejection as to the remaining claims, as hereinafter set forth.

Gofuku discloses a method of fabricating a semiconductor device that includes depositing an insulating film and etching an opening therein. Gofuku at column 5, lines 58-62. The opening exposes a portion of a contact region in an N-type blocking layer. Wiring electrodes, formed from AlSi, are formed in the opening. *Id.* at column 5, line 63 through column 6, line 3.

A claim is anticipated only if each and every element as set forth in the claim is found, either expressly or inherently described, in a single prior art reference. *Verdegaal Brothers v.*

*Union Oil Co. of California*, 2 U.S.P.Q.2d 1051, 1053 (Fed. Cir. 1987). The identical invention must be shown in as complete detail as is contained in the claim. *Richardson v. Suzuki Motor Co.*, 9 U.S.P.Q.2d 1913, 1920 (Fed. Cir. 1989).

Gofuku does not expressly or inherently describe each and every element of amended claim 1 because Gofuku does not disclose the element of “forming a single layer of metal having a substantially planar top surface upon a top planar surface of the insulation layer, . . . wherein the single layer of metal comprises a material selected from the group consisting of AlAg, AlAu, AlMn, AlNa, AlW, AlCuZn, and AlNi.” Rather, the wiring electrode of Gofuku is formed from AlSi.

Since Gofuku does not expressly or inherently describe each and every element of claim 1, the anticipation rejection is improper and should be withdrawn.

Claims 6 and 11 are allowable, *inter alia*, as depending from an allowable base claim.

Anticipation Rejection Based on U.S. Patent No. 5,960,304 to McAnally *et al.*

Claims 1, 5, and 6 stand rejected under 35 U.S.C. § 102(e) as being anticipated by U.S. Patent No. 5,960,304 to McAnally *et al.* (“McAnally”). Applicants respectfully traverse this rejection, as hereinafter set forth.

McAnally discloses a method of forming a contact to a substrate. McAnally at column 2, lines 43-45. A first stopping layer, an insulating layer, and a second stopping layer are formed over the substrate and are etched to form the contact. *Id.* at column 2, line 52 through column 3, line 67. The contact is filled with a conductive material. *Id.* at column 4, lines 15-17.

McAnally does not expressly or inherently describe each and every element of amended claim 1 because McAnally does not disclose the element of “forming a single layer of metal having a substantially planar top surface upon a top planar surface of the insulation layer, . . . wherein the single layer of metal comprises a material selected from the group consisting of AlAg, AlAu, AlMn, AlNa, AlW, AlCuZn, and AlNi.”

Since McAnally does not expressly or inherently describe each and every element of claim 1, the anticipation rejection is improper and should be withdrawn.

Claims 5 and 6 are allowable, *inter alia*, as depending from an allowable base claim.

**35 U.S.C. § 103(a) Obviousness Rejections**

Obviousness Rejection Based on Gofuku in view of U.S. Patent No. 5,355,020 to Lee *et al.* and U.S. Patent No. 5,840,623 to Sahota

Dependent claims 7 and 8 stand rejected under 35 U.S.C. § 103(a) as being unpatentable over Gofuku in view of U.S. Patent No. 5,355,020 to Lee *et al.* (“Lee”) and U.S. Patent No. 5,840,623 to Sahota (“Sahota”). Applicants respectfully traverse this rejection, as hereinafter set forth. Since claims 7 and 8 are dependent claims, these claims are allowable, *inter alia*, as depending from an allowable base claim.

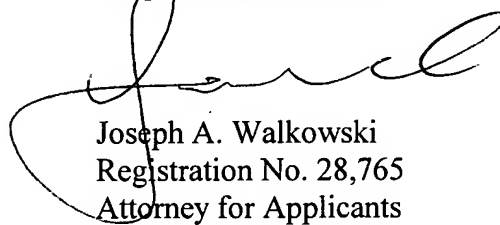
### ENTRY OF AMENDMENTS

The amendments to claims 1, 6-8, 11, 14, 15, 19, and 21 should be entered by the Examiner because the amendments are supported by the as-filed specification and drawings and do not add new matter to the application.

### CONCLUSION

Claims 1, 5-8, and 11-21 are believed to be in condition for allowance, and an early notice thereof is respectfully solicited. Should the Examiner determine that additional issues remain which might be resolved by a telephone conference, she is respectfully invited to contact Applicants' undersigned attorney.

Respectfully submitted,



Joseph A. Walkowski  
Registration No. 28,765  
Attorney for Applicants  
TRASKBRITT  
P.O. Box 2550  
Salt Lake City, Utah 84110-2550  
Telephone: 801-532-1922

Date: November 14, 2006

KAH/sfc:slm  
Document in ProLaw